



# <u>DDA (LO-R1) H</u>

PNP PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

#### Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available
   (DDC)
- Built-In Biasing Resistors
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

# Mechanical Data Case: SOT-563

P/N

DDA122LH

DDA142JH

DDA122TH

DDA142TH

- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42
- leadframe. Solderable per MIL-STD-202, Method 208
  Terminal Connections: See Diagram
- Weight: 0.005 grams (approximate)

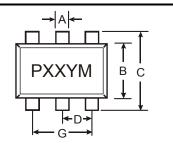
R1 (NOM)

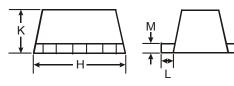
0.22KΩ

0.47KΩ

0.22KΩ

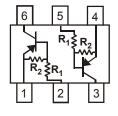
0.47KΩ

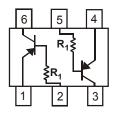




SOT-563										
Dim	Min Max Typ									
Α	0.15	0.30	0.25							
В	1.10	1.20								
С	1.55	1.60								
D	0.50									
G	0.90	1.00								
Н	1.50	1.70	1.60							
К	0.56	0.60	0.60							
L	0.15	0.25	0.20							
М	0.10	0.18	0.11							
All D	All Dimensions in mm									

SEE NOTE 1





R1 Only

R1, R2

SCHEMATIC DIAGRAM, TOP VIEW

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

R2 (NOM)

10KΩ

10KΩ

OPEN

OPEN

MARKING

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Characteristic		Symbol	Value	Unit	
Supply Voltage (6) to (1) and (3) to (4)		Vcc	-50	V	
Input Voltage (2) to (1) and (5) to (4)	DDA122LH DDA142JH	V <sub>IN</sub>	+5 to -6 +5 to -6	V	
Input Voltage (1) to (2) and (4) to (5)	DDA122TH DDA142TH	V <sub>EBO (MAX)</sub>	-5	V	
Output Current	All	Ic	-100	mA	
Power Dissipation		Pd	150	mW	
Thermal Resistance, Junction to Ambient Air	(Note 2)	$R_{ heta}$ JA	833	°C/W	
Operating and Storage Temperature Range		T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes: 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

2. Mounted on FR4 Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.

3. No purposefully added lead.

4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics	@T <sub>A</sub> = 25°C unless otherwise specified	R1, R2 Types
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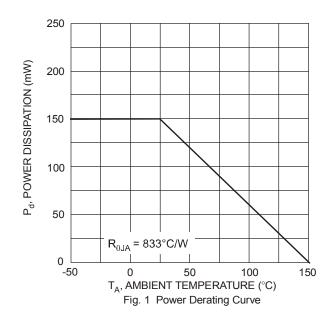
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Input Voltage	DDA122LH DDA142JH	V <sub>I(off)</sub>	-0.3 -0.3	_	_	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	DDA122LH DDA142JH	V <sub>l(on)</sub>	_	_	-2.0 -2.0	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA
Output Voltage		V <sub>O(on)</sub>	_	_	-0.3V	V	I <sub>O</sub> /I <sub>I</sub> = -5mA/-0.25mA
Input Current	DDA122LH DDA142JH	lı	_	_	-28 -13	mA	V <sub>1</sub> = -5V
Output Current		I <sub>O(off)</sub>	_	_	-0.5	μA	$V_{CC} = -50V, V_{I} = 0V$
DC Current Gain	DDA122LH DDA142JH	GI	56 56	_		_	V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA
Gain-Bandwidth Product*		f⊤	_	200		MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100MHz

\* Transistor - For Reference Only

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified **R1-Only**

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage		BV <sub>CBO</sub>	-50			V	I <sub>C</sub> = -50μA
Collector-Emitter Breakdown Voltage	!	BV <sub>CEO</sub>	-40	_	_	V	I <sub>C</sub> = -1mA
Emitter-Base Breakdown Voltage	DDA122TH DDA142TH	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -50μA I <sub>E</sub> = -50μA
Collector Cutoff Current		I <sub>CBO</sub>	—	—	-0.5	μA	V <sub>CB</sub> = -50V
Emitter Cutoff Current DDA122TH DDA142TH		I <sub>EBO</sub>			-0.5 -0.5	μA	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	_	_	-0.3	v	I <sub>C</sub> = -5mA, I <sub>B</sub> = -0.25mA
DC Current Transfer Ratio	DDA122TH DDA142TH	h <sub>FE</sub>	100 100	250 250	600 600	_	I <sub>C</sub> = -1mA, V <sub>CE</sub> = -5V
Gain-Bandwidth Product*		f <sub>T</sub>	_	200		MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz

\* Transistor - For Reference Only



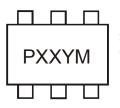


### Ordering Information (Note 6)

Device	Packaging	Shipping		
DDA122LH-7	SOT-563	3000/Tape & Reel		
DDA142JH-7	SOT-563	3000/Tape & Reel		
DDA122TH-7	SOT-563	3000/Tape & Reel		
DDA142TH-7	SOT-563	3000/Tape & Reel		

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**



XXX = Product Type Marking Code (See Page 1) YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

#### Date Code Key

Year	2002	2003	2004	200	5 20	06 20	007	2008	2009	2010	2011	2012
Code	Ν	Р	R	S	Т	-	U	V	W	Х	Y	Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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